

Supporting Information

Effect of geometry of precursor crucibles on the growth of MoS₂ flakes by chemical vapor deposition

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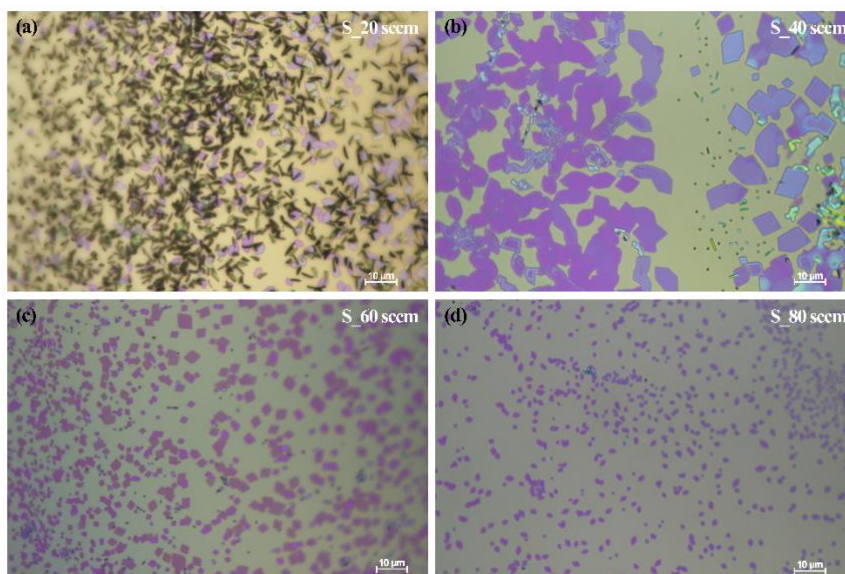


Fig. S1. OM images of deposits obtained with S crucibles at different Ar gas flow rates. (a) 20 sccm, (b) 40 sccm, (c) 60 sccm and (d) 80 sccm.

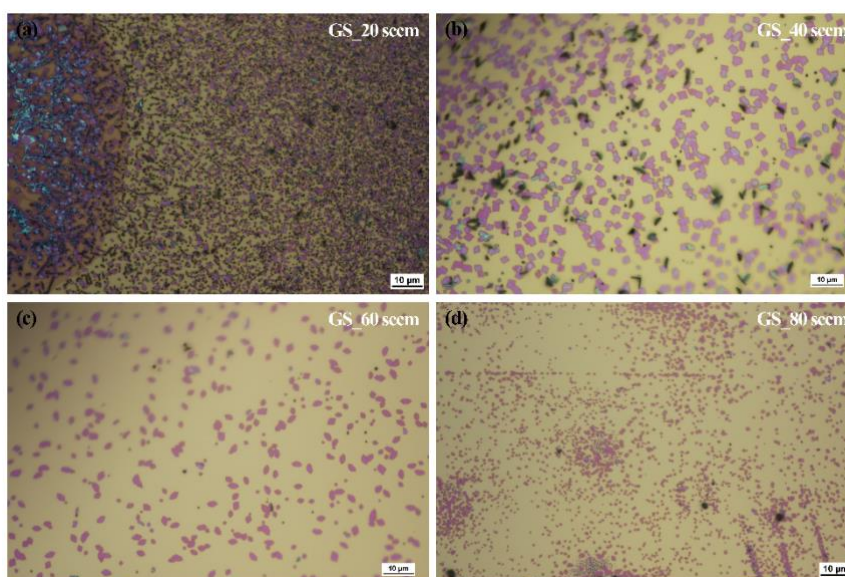


Fig. S2. OM images of deposits obtained with GS crucibles at different Ar gas flow rates. (a) 20 sccm, (b) 40 sccm, (c) 60 sccm and (d) 80 sccm.

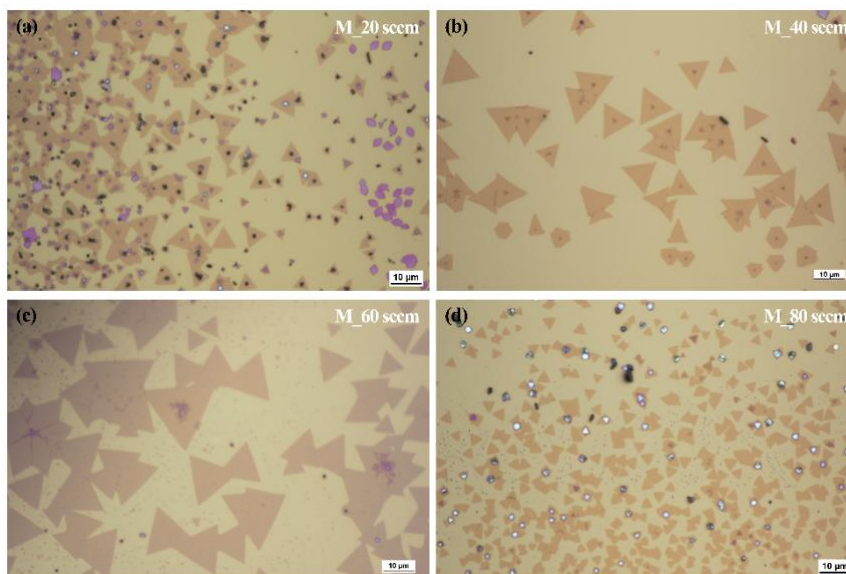


Fig. S3. OM images of deposits obtained with M crucibles at different Ar gas flow rates. (a) 20 sccm, (b) 40 sccm, (c) 60 sccm and (d) 80 sccm.

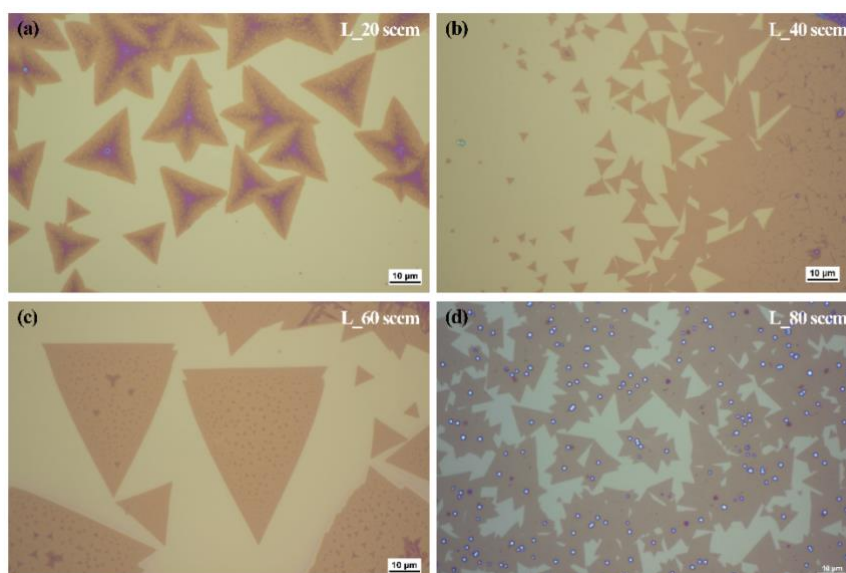


Fig. S4. OM images of deposits obtained with L crucibles at different Ar gas flow rates. (a) 20 sccm, (b) 40 sccm, (c) 60 sccm and (d) 80 sccm.